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NOTICE OF ALLOWANCE AND FEE(S) DUE

31780 7590 01/09/2013
Robinson Intellectual Property Law Office, P.C.
3975 Fair Ridge Drive
Suite 20 North
Fairfax, VA 22033

EXAMINER

PADGETT, MARIANNE L

ART UNIT

PAPER NUMBER

1717

DATE MAILED: 01/09/2013

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
08/169,127	12/20/1993	HISATO SHINOHARA	0756-0945	2677

TITLE OF INVENTION: LASER IRRADIATION METHOD

APPLN. TYPE	SMALL ENTITY	ISSUE FEE DUE	PUBLICATION FEE DUE	PREV. PAID ISSUE FEE	TOTAL FEE(S) DUE	DATE DUE
nonprovisional	NO	\$0	\$0	\$1770	\$0	04/09/2013

THE APPLICATION IDENTIFIED ABOVE HAS BEEN EXAMINED AND IS ALLOWED FOR ISSUANCE AS A PATENT. PROSECUTION ON THE MERITS IS CLOSED. THIS NOTICE OF ALLOWANCE IS NOT A GRANT OF PATENT RIGHTS. THIS APPLICATION IS SUBJECT TO WITHDRAWAL FROM ISSUE AT THE INITIATIVE OF THE OFFICE OR UPON PETITION BY THE APPLICANT. SEE 37 CFR 1.313 AND MPEP 1308.

THE ISSUE FEE AND PUBLICATION FEE (IF REQUIRED) MUST BE PAID WITHIN THREE MONTHS FROM THE MAILING DATE OF THIS NOTICE OR THIS APPLICATION SHALL BE REGARDED AS ABANDONED. THIS STATUTORY PERIOD CANNOT BE EXTENDED. SEE 35 U.S.C. 151. THE ISSUE FEE DUE INDICATED ABOVE DOES NOT REFLECT A CREDIT FOR ANY PREVIOUSLY PAID ISSUE FEE IN THIS APPLICATION. IF AN ISSUE FEE HAS PREVIOUSLY BEEN PAID IN THIS APPLICATION (AS SHOWN ABOVE), THE RETURN OF PART B OF THIS FORM WILL BE CONSIDERED A REQUEST TO REAPPLY THE PREVIOUSLY PAID ISSUE FEE TOWARD THE ISSUE FEE NOW DUE.

HOW TO REPLY TO THIS NOTICE:

I. Review the SMALL ENTITY status shown above.

If the SMALL ENTITY is shown as YES, verify your current SMALL ENTITY status:

A. If the status is the same, pay the TOTAL FEE(S) DUE shown above.

B. If the status above is to be removed, check box 5b on Part B - Fee(s) Transmittal and pay the PUBLICATION FEE (if required) and twice the amount of the ISSUE FEE shown above, or

If the SMALL ENTITY is shown as NO:

A. Pay TOTAL FEE(S) DUE shown above, or

B. If applicant claimed SMALL ENTITY status before, or is now claiming SMALL ENTITY status, check box 5a on Part B - Fee(s) Transmittal and pay the PUBLICATION FEE (if required) and 1/2 the ISSUE FEE shown above.

II. PART B - FEE(S) TRANSMITTAL, or its equivalent, must be completed and returned to the United States Patent and Trademark Office (USPTO) with your ISSUE FEE and PUBLICATION FEE (if required). If you are charging the fee(s) to your deposit account, section "4b" of Part B - Fee(s) Transmittal should be completed and an extra copy of the form should be submitted. If an equivalent of Part B is filed, a request to reapply a previously paid issue fee must be clearly made, and delays in processing may occur due to the difficulty in recognizing the paper as an equivalent of Part B.

III. All communications regarding this application must give the application number. Please direct all communications prior to issuance to Mail Stop ISSUE FEE unless advised to the contrary.

IMPORTANT REMINDER: Utility patents issuing on applications filed on or after Dec. 12, 1980 may require payment of maintenance fees. It is patentee's responsibility to ensure timely payment of maintenance fees when due.

PART B - FEE(S) TRANSMITTAL

**Complete and send this form, together with applicable fee(s), to: Mail Mail Stop ISSUE FEE
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INSTRUCTIONS: This form should be used for transmitting the ISSUE FEE and PUBLICATION FEE (if required). Blocks 1 through 5 should be completed where appropriate. All further correspondence including the Patent, advance orders and notification of maintenance fees will be mailed to the current correspondence address as indicated unless corrected below or directed otherwise in Block 1, by (a) specifying a new correspondence address; and/or (b) indicating a separate "FEE ADDRESS" for maintenance fee notifications.

CURRENT CORRESPONDENCE ADDRESS (Note: Use Block 1 for any change of address)

Note: A certificate of mailing can only be used for domestic mailings of the Fee(s) Transmittal. This certificate cannot be used for any other accompanying papers. Each additional paper, such as an assignment or formal drawing, must have its own certificate of mailing or transmission.

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Certificate of Mailing or Transmission

I hereby certify that this Fee(s) Transmittal is being deposited with the United States Postal Service with sufficient postage for first class mail in an envelope addressed to the Mail Stop ISSUE FEE address above, or being facsimile transmitted to the USPTO (571) 273-2885, on the date indicated below.

(Depositor's name)
(Signature)
(Date)

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EXAMINER	ART UNIT	CLASS-SUBCLASS
PADGETT, MARIANNE L	1717	438-487000

1. Change of correspondence address or indication of "Fee Address" (37 CFR 1.363).

☐ Change of correspondence address (or Change of Correspondence Address form PTO/SB12) attached;

☐ "Fee Address" indication (or "Fee Address" Indication form PTO/SB17; Rev 03-02 or more recent) attached. Use of a **Customer Number is required.**

2. For printing on the patent front page, list

- | | |
|--|---|
| (1) the names of up to 3 registered patent attorneys or agents OR, alternatively, | 1 |
| (2) the name of a single firm (having as a member a registered attorney or agent) and the names of up to 2 registered patent attorneys or agents. If no name is listed, no name will be printed. | 2 |
| | 3 |

3. ASSIGNEE NAME AND RESIDENCE DATA TO BE PRINTED ON THE PATENT (print or type)

PLEASE NOTE: Unless an assignee is identified below, no assignee data will appear on the patent. If an assignee is identified below, the document has been filed for recordation as set forth in 37 CFR 3.111. Completion of this form is NOT a substitute for filing an assignment.

(A) NAME OF ASSIGNEE

(B) RESIDENCE: (CITY and STATE OR COUNTRY)

Please check the appropriate assignee category or categories (will not be printed on the patent): ☐ Individual ☐ Corporation or other private group entity ☐ Government

4a. The following fee(s) are submitted:

- ☐ Issue Fee
☐ Publication Fee (No small entity discount permitted)
☐ Advance Order - # of Copies _____

4b. Payment of Fee(s): (Please first reapply any previously paid issue fee shown above)

- ☐ A check is enclosed.
☐ Payment by credit card. Form PTO-2038 is attached.
☐ The Director is hereby authorized to charge the required fee(s), any deficiency, or credit any overpayment, to Deposit Account Number _____ (enclose an extra copy of this form).

5. **Change in Entity Status** (from status indicated above)

- ☐ a. Applicant claims SMALL ENTITY status. See 37 CFR 1.27. ☐ b. Applicant is no longer claiming SMALL ENTITY status. See 37 CFR 1.27(g)(2).

NOTE: The Issue Fee and Publication Fee (if required) will not be accepted from anyone other than the applicant; a registered attorney or agent; or the assignee or other party in interest as shown by the records of the United States Patent and Trademark Office.

Authorized Signature _____ Date _____
Typed or printed name _____ Registration No. _____

This collection of information is required by 37 CFR 1.311. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 12 minutes to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, Virginia 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, Virginia 22313-1450.

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Determination of Patent Term Extension or Adjustment under 35 U.S.C. 154 (b) (application filed prior to June 8, 1995)

This patent application was filed prior to June 8, 1995, thus no Patent Term Extension or Adjustment applies.

Any questions regarding the Patent Term Extension or Adjustment determination should be directed to the Office of Patent Legal Administration at (571)-272-7702. Questions relating to issue and publication fee payments should be directed to the Customer Service Center of the Office of Patent Publication at 1-(888)-786-0101 or (571)-272-4200.

Privacy Act Statement

The Privacy Act of 1974 (P.L. 93-579) requires that you be given certain information in connection with your submission of the attached form related to a patent application or patent. Accordingly, pursuant to the requirements of the Act, please be advised that: (1) the general authority for the collection of this information is 35 U.S.C. 2(b)(2); (2) furnishing of the information solicited is voluntary; and (3) the principal purpose for which the information is used by the U.S. Patent and Trademark Office is to process and/or examine your submission related to a patent application or patent. If you do not furnish the requested information, the U.S. Patent and Trademark Office may not be able to process and/or examine your submission, which may result in termination of proceedings or abandonment of the application or expiration of the patent.

The information provided by you in this form will be subject to the following routine uses:

1. The information on this form will be treated confidentially to the extent allowed under the Freedom of Information Act (5 U.S.C. 552) and the Privacy Act (5 U.S.C. 552a). Records from this system of records may be disclosed to the Department of Justice to determine whether disclosure of these records is required by the Freedom of Information Act.
2. A record from this system of records may be disclosed, as a routine use, in the course of presenting evidence to a court, magistrate, or administrative tribunal, including disclosures to opposing counsel in the course of settlement negotiations.
3. A record in this system of records may be disclosed, as a routine use, to a Member of Congress submitting a request involving an individual, to whom the record pertains, when the individual has requested assistance from the Member with respect to the subject matter of the record.
4. A record in this system of records may be disclosed, as a routine use, to a contractor of the Agency having need for the information in order to perform a contract. Recipients of information shall be required to comply with the requirements of the Privacy Act of 1974, as amended, pursuant to 5 U.S.C. 552a(m).
5. A record related to an International Application filed under the Patent Cooperation Treaty in this system of records may be disclosed, as a routine use, to the International Bureau of the World Intellectual Property Organization, pursuant to the Patent Cooperation Treaty.
6. A record in this system of records may be disclosed, as a routine use, to another federal agency for purposes of National Security review (35 U.S.C. 181) and for review pursuant to the Atomic Energy Act (42 U.S.C. 218(c)).
7. A record from this system of records may be disclosed, as a routine use, to the Administrator, General Services, or his/her designee, during an inspection of records conducted by GSA as part of that agency's responsibility to recommend improvements in records management practices and programs, under authority of 44 U.S.C. 2904 and 2906. Such disclosure shall be made in accordance with the GSA regulations governing inspection of records for this purpose, and any other relevant (i.e., GSA or Commerce) directive. Such disclosure shall not be used to make determinations about individuals.
8. A record from this system of records may be disclosed, as a routine use, to the public after either publication of the application pursuant to 35 U.S.C. 122(b) or issuance of a patent pursuant to 35 U.S.C. 151. Further, a record may be disclosed, subject to the limitations of 37 CFR 1.14, as a routine use, to the public if the record was filed in an application which became abandoned or in which the proceedings were terminated and which application is referenced by either a published application, an application open to public inspection or an issued patent.
9. A record from this system of records may be disclosed, as a routine use, to a Federal, State, or local law enforcement agency, if the USPTO becomes aware of a violation or potential violation of law or regulation.

Notice of Allowability**Application No.**

08/169,127

Applicant(s)

SHINOHARA ET AL.

Examiner

MARIANNE L. PADGETT

Art Unit

1717

- The MAILING DATE of this communication appears on the cover sheet with the correspondence address-

All claims being allowable, PROSECUTION ON THE MERITS IS (OR REMAINS) CLOSED in this application. If not included herewith (or previously mailed), a Notice of Allowance (PTOL-85) or other appropriate communication will be mailed in due course. **THIS NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RIGHTS.** This application is subject to withdrawal from issue at the initiative of the Office or upon petition by the applicant. See 37 CFR 1.313 and MPEP 1308.

1. ☒ This communication is responsive to 12/8/11, 10/17/12 & 12/13/2012.
2. ☐ An election was made by the applicant in response to a restriction requirement set forth during the interview on ____; the restriction requirement and election have been incorporated into this action.
3. ☒ The allowed claim(s) is/are 176-180. As a result of the allowed claim(s), you may be eligible to benefit from the **Patent Prosecution Highway** program at a participating intellectual property office for the corresponding application. For more information, please see http://www.uspto.gov/patents/init_events/pph/index.jsp or send an inquiry to PPHfeedback@uspto.gov.
4. ☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
- a) ☐ All b) ☐ Some* c) ☐ None of the:
1. ☐ Certified copies of the priority documents have been received.
2. ☐ Certified copies of the priority documents have been received in Application No. ____.
3. ☐ Copies of the certified copies of the priority documents have been received in this national stage application from the International Bureau (PCT Rule 17.2(a)).

* Certified copies not received: ____.

Applicant has **THREE MONTHS FROM THE "MAILING DATE"** of this communication to file a reply complying with the requirements noted below. Failure to timely comply will result in ABANDONMENT of this application.

THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.

5. ☐ CORRECTED DRAWINGS (as "replacement sheets") must be submitted.
- ☐ including changes required by the attached Examiner's Amendment / Comment or in the Office action of Paper No./Mail Date ____.
- Identifying indicia such as the application number (see 37 CFR 1.84(c)) should be written on the drawings in the front (not the back) of each sheet. Replacement sheet(s) should be labeled as such in the header according to 37 CFR 1.121(d).**
6. ☐ DEPOSIT OF and/or INFORMATION about the deposit of BIOLOGICAL MATERIAL must be submitted. Note the attached Examiner's comment regarding REQUIREMENT FOR THE DEPOSIT OF BIOLOGICAL MATERIAL.

Attachment(s)

1. ☐ Notice of References Cited (PTO-892)
2. ☐ Information Disclosure Statements (PTO/SB/08),
Paper No./Mail Date ____
3. ☐ Examiner's Comment Regarding Requirement for Deposit
of Biological Material
4. ☐ Interview Summary (PTO-413),
Paper No./Mail Date ____
5. ☒ Examiner's Amendment/Comment
6. ☐ Examiner's Statement of Reasons for Allowance
7. ☐ Other ____.

/MARIANNE L. PADGETT/
Primary Examiner, Art Unit 1717

An Examiner's Amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

In the claims:

Cancel claims 61-80, 91-94, 101, 104-107, 131 & 140-175, due to the December 8, 2011 CAFC judgment.

Please **amend** claims 176-180, as follows, to place them in independent form (*as per* MPEP 1214.06 I & II, which claims are identical in substance to the allowed claims of the vacated 7/20/2012 action, but are amended so as to follow the official form, in response to the 10/17/12 petition):

176. ~~The method according to claim 64. A method of manufacturing an active matrix display device having an active~~

~~matrix circuit and a driving circuit, said method comprising:~~

~~forming an ion blocking film over a substrate;~~

~~forming a non-single crystalline semiconductor layer;~~

~~providing a first laser beam having a first cross section;~~

~~expanding said first cross section of the first pulsed laser beam along a first direction;~~

~~condensing the expanded laser beam along a second direction orthogonal to said first direction;~~

~~irradiating the non-single crystalline semiconductor layer with the condensed laser beam having a second cross section at a surface of the non-single crystalline semiconductor layer wherein a length of said second cross section along said first direction is longer than that of said first cross section and a width of said second cross section along said second direction is smaller than that of said first cross section;~~

~~moving a relative location of said substrate to the condensed laser beam along a third direction orthogonal to said first direction while irradiating the non-single crystalline semiconductor layer with the condensed laser beam whereby the non-single crystalline semiconductor layer is crystallized;~~

~~removing an insulating layer comprising silicon oxide from an upper surface of the crystallized semiconductor layer, wherein said insulating layer comprising silicon oxide is formed before the irradiating with the condensed laser beam; and~~

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forming a plurality of thin film transistors using the crystallized semiconductor layer as at least channel regions of the thin film transistors for the active matrix circuit and said driving circuit.

177. The method according to claim 74 A method of manufacturing an active matrix display device having an active matrix circuit and a peripheral circuit for driving pixel TFTs, said method comprising:

forming an ion blocking film over a substrate;
forming a non-single crystalline semiconductor layer over said ion blocking film;
providing a first laser beam having a first cross section;
expanding said first cross section of the first pulsed laser beam along a first direction;

condensing the expanded laser beam along a second direction orthogonal to said first direction;

irradiating the non-single crystalline semiconductor layer with the condensed laser beam having a second cross section at a surface of the non-single crystalline semiconductor layer wherein a length of said second cross section along said first direction is longer than that of said first cross section and a width of said second cross section along said second direction is smaller than that of said first cross section;

moving a relative location of said substrate to the condensed laser beam along a third direction orthogonal to said first direction while irradiating the non-single crystalline semiconductor layer with the condensed laser beam whereby the non-single crystalline semiconductor layer is crystallized;

removing an insulating layer comprising silicon oxide from an upper surface of the crystallized semiconductor layer, wherein said insulating layer comprising silicon oxide is formed before the irradiating with the condensed laser beam; and

forming a plurality of thin film transistors using the crystallized semiconductor layer as at least channel regions of the thin film transistors for the active matrix circuit and said peripheral circuit.

178. The method according to claim 144 A method of manufacturing an active matrix display device having an active matrix circuit and a driving circuit, said method comprising:

forming an ion blocking film over a substrate;
forming a non-single crystalline semiconductor layer over said ion blocking film, said non-single crystalline semiconductor layer being substantially intrinsic and doped with a dopant selected from the group consisting of boron and arsenic;
providing a first laser beam having a first cross section;
expanding said first cross section of the first pulsed laser beam along a first direction;

condensing the expanded laser beam along a second direction orthogonal to said first direction;

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irradiating the non-single crystalline semiconductor layer with the condensed laser beam having a second cross section at a surface of the non-single crystalline semiconductor layer wherein a length of said second cross section along said first direction is longer than that of said first cross section and a width of said second cross section along said second direction is smaller than that of said first cross section;

moving a relative location of said substrate to the condensed laser beam along a third direction orthogonal to said first direction while irradiating the non-single crystalline semiconductor layer with the condensed laser beam whereby the non-single crystalline semiconductor layer is crystallized;

removing an insulating layer comprising silicon oxide from an upper surface of the crystallized semiconductor layer, wherein said insulating layer comprising silicon oxide is formed before the irradiating with the condensed laser beam; and

forming a plurality of thin film transistors using the crystallized semiconductor layer as at least channel regions of the thin film transistors for the active matrix circuit and said driving circuit.

179. The method according to claim 154A method of manufacturing a plurality of thin film transistors, comprising steps of:

forming an ion blocking film over a substrate;
forming a non-single crystalline semiconductor layer over said ion blocking film;
providing a first laser beam having a first cross section;
expanding said first cross section of the first pulsed laser beam along a first direction;

condensing the expanded laser beam along a second direction orthogonal to said first direction;

irradiating the non-single crystalline semiconductor layer with the condensed laser beam having a second cross section at a surface of the non-single crystalline semiconductor layer wherein a length of said second cross section along said first direction is longer than that of said first cross section and a width of said second cross section along said second direction is smaller than that of said first cross section;

moving a relative location of said substrate to the condensed laser beam along a third direction orthogonal to said first direction while irradiating the non-single crystalline semiconductor layer with the condensed laser beam whereby the non-single crystalline semiconductor layer is crystallized;

removing an insulating layer comprising silicon oxide from an upper surface of the crystallized semiconductor layer, wherein said insulating layer comprising silicon oxide is formed before the irradiating with the condensed laser beam; and

forming a plurality of thin film transistors using the crystallized semiconductor layer as at least channel regions of the thin film transistors.

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180. ~~The method according to claim 168~~A method of manufacturing an active matrix display device having an active matrix circuit and a peripheral circuit for driving pixel TFTs, said method comprising:

forming an ion blocking film over a substrate;

forming a non-single crystalline semiconductor layer over said ion blocking, said non-single crystalline semiconductor layer being substantially intrinsic and doped with a dopant selected from the group consisting of boron and arsenic;

providing a first laser beam having a first cross section;

expanding said first cross section of the first pulsed laser beam a first direction;

condensing the expanded laser beam along a second direction orthogonal to said first direction;

irradiating the non-single crystalline semiconductor layer with the condensed laser beam having a second cross section at a surface of the semiconductor layer wherein a length of said second cross section along said first direction is longer than that of said first cross section and a width of said second cross section along said second direction is smaller than that of said first cross section;

moving a relative location of said substrate to the condensed laser beam along a third direction orthogonal to said first direction so that the semiconductor layer is scanned with the condensed laser beam and whereby the semiconductor layer is crystallized;

removing an insulating layer comprising silicon oxide from an upper surface of the crystallized semiconductor layer, wherein said insulating layer comprising silicon oxide is formed before the irradiating with the condensed laser beam; and

forming a plurality of thin film transistors using the crystallized semiconductor layer as at least channel regions of the thin film transistors for said active matrix circuit and said peripheral circuit.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to **Marianne L. Padgett** whose telephone number is **(571) 272-1425**. The examiner can normally be reached on M-F from about 9:00 a.m. to 5:00 p.m.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Dah-Wei Yuan, can be reached at (571) 272-1295. The fax phone number for the organization where this application or proceeding is assigned is (571) 273-8300.

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Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

/Marianne L. Padgett/
Primary Examiner, Art Unit 1717

MLP/dictation software

1/3/2013